Call for Papers

Special Section on Fundamentals and Applications of Advanced Semiconductor Devices

The IEICE (Institute of Electronics, Information and Communication Engineers) Transactions on Electronics announce a Special Section on “Fundamentals and Applications of Advanced Semiconductor Devices” to be published in October 2022. As digital processing units penetrate deeply into information society, the demand for high-performance semiconductor devices is kept growing. The purpose of this Special Section is to discuss various aspects of advanced semiconductor devices from fundamental physics to circuit applications. These include Si-based MOSFETs and bipolar transistors, compound semiconductor devices, and nano-scale devices.

1. Scope

Contributions are solicited in the following areas (but are not limited to these areas):

- Advanced integration technologies
- MOS/bipolar devices technologies
- ULSI process technologies
- Compound semiconductor materials and devices
- High-speed devices and circuits
- Microwave/Millimeter-wave devices and circuits
- Power devices
- TFT materials, devices and circuits
- Wide bandgap materials and devices
- Quantum effect/single electron devices
- Novel devices and circuits
- Characterization and simulation
- Semiconductor devices applications
- Sensors and displays

2. Submission Instructions

The deadline for submission is October 18, 2021. Types of manuscripts should be either “Paper (within 8 pages)” or “Brief Paper (within 4 pages).” Manuscripts should be prepared according to the “Information for Authors,” the latest version of which is available at: https://www.ieice.org/eng/shiori/mokuji_es.html.

This special section will accept only papers by electronic submission. Prospective authors are requested to follow the submission procedure described below.

Submit a paper and transfer copyright of the paper using the IEICE Web site https://review.ieice.org/regist/regist_baseinfo_e.aspx. Authors should choose the [Special-FU] Fundamentals and Applications of Advanced Semiconductor Devices as a "Issue/Section" on the online screen. Do not choose [Regular-EC].

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[IMPORTANT NOTICE]

* Upon accepted for publication, all authors, including authors of invited papers, should pay the page charges covering partial the cost of publication around March 2022. If payment is not completed by 15 April, 2022, your manuscript will be handled as rejection.

* The accepted papers will be published online soon on the web site of Transactions Online after the payment of article processing charges been completed. For detailed information, please visit https://www.ieice.org/eng/shiori/page2_es.html#8.

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